3 A High-Speed MOSFET Drivers

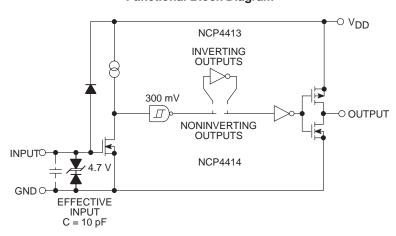
The NCP4413/4414 are 3 A CMOS buffer/drivers. They will not latch up under any conditions within their power and voltage ratings. They are not subject to damage when up to 5 V of noise spiking of either polarity that occurs on the ground pin. They can accept, without damage or logic upset, up to 500 mA of current of either polarity being forced back into their output. All terminals are fully protected against up to 4 kV of electrostatic discharge.

As MOSFET drivers, the NCP4413/4414 can easily switch 1800 pF gate capacitance in 20 nsec with matched rise and fall times, and provide low enough impedance in both the ON and the OFF states to ensure the MOSFET's intended state will not be affected, even by large transients. The rise and fall time edges are matched to allow driving short–duration inputs with greater output accuracy.

Features

- Latch-up Protected: Will Withstand 500 mA Reverse Current
- Input Will Withstand Negative Inputs Up to 5 V
- ESD Protected (4 kV)
- High Peak Output Current (3 A)
- Wide Operating Range (4.5 V to 16 V)
- High Capacitive Load Drive Capability (1800 pF in 20 nsec)
- Short Delay Time (35 nsec Typ)
- Consistent Delay Times with Changes in Supply Voltage
- Matched Delay Times
- Low Supply Current
 With Logic "1" Input (500 μA)
 With Logic "0" Input (100 μA)
- Low Output Impedance (2.7 Ω)

Functional Block Diagram





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MARKING DIAGRAM



SO-8 D SUFFIX CASE 751





PDIP-8 P SUFFIX CASE 626



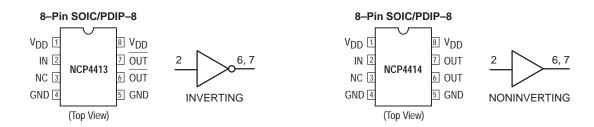
= Device Number (3 or 4)

YY, Y = Year
WW, W = Work Week
X = Assembly ID Code
Z = Subcontractor ID Code
CO = Country of Origin

ORDERING INFORMATION

Device	Package	Shipping		
NCP4413DR2 Inverting	SO-8	2500 Tape & Reel		
NCP4413P Inverting	PDIP-8	50 Units/Rail		
NCP4414DR2 Non–Inverting	SO-8	2500 Tape & Reel		
NCP4414P Non–Inverting	PDIP-8	50 Units/Rail		

PIN CONNECTIONS



NC = NO INTERNAL CONNECTION

ABSOLUTE MAXIMUM RATINGS*

Rating	Symbol	Value	Unit
Supply Voltage	V _{DD}	+20	V
Input Voltage, IN A or IN B	VIN	V _{DD} + 0.3 to GND – 5.0	V
Maximum Chip Temperature		+150	°C
Storage Temperature Range	T _{stg}	-65 to +150	°C
Lead Temperature (Soldering, 10 sec)	T _{SOI}	+300	°C
Package Thermal Resistance SOIC SOIC	R _θ JA R _θ JC	155 45	°C/W
Operating Temperature Range	TA	-40 to +85	°C
Power Dissipation ($T_A \le 70^{\circ}C$) SOIC	PD	470	mW

^{*}Static—sensitive device. Unused devices must be stored in conductive material. Protect devices from static discharge and static fields. Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operation section of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS (Over operating temperature range with 4.5 V \leq V_{DD} \leq 16 V, unless otherwise specified. Typical values are measured at T_A = 25°C; V_{DD} = 16 V.)

Characteristic	Symbol	Test Conditions		Min	Тур	Max	Unit
Input							
Logic 1 High Input Voltage	VIH	_		2.0	_	_	V
Logic 0 Low Input Voltage	VIL	-	-	_	-	0.8	V
Input Current	IIN	$0V \le V_{IN} \le V_{DD}$	$T_A = 25^{\circ}C$ $-40^{\circ}C \le T_A \le 85^{\circ}C$	-1.0 -10	- -	1.0 10	μА
Output							•
High Output Voltage	Vон	DC Test		V _{DD} - 0.025	-	_	V
Low Output Voltage	VOL	DC Test		-	-	0.025	٧
Output Resistance	RO	$V_{DD} = 16 \text{ V}, I_{O} = 10 \text{ mA}$	$T_A = 25^{\circ}C$ $-40^{\circ}C \le T_A \le 85^{\circ}C$	- -	2.7 3.3	4.0 5.0	Ω
Peak Output Current	I _{PK}	V _{DD} = 16 V		-	3.0	_	Α
Latch–Up Protection Withstand Reverse Current	I _{REV}	Duty Cycle ≤ 2% t ≤ 300 μsec	V _{DD} = 16 V	0.5	-	_	А
Switching Time (Note 1.)							•
Rise Time	t _R	Figure 1	$T_A = 25^{\circ}C$ $-40^{\circ}C \le T_A \le 85^{\circ}C$		20 24	28 33	nsec
Fall Time	tF	Figure 1	$T_A = 25^{\circ}C$ $-40^{\circ}C \le T_A \le 85^{\circ}C$	_ _	20 24	28 33	nsec
Delay Time	t _{D1}	Figure 1	$T_A = 25^{\circ}C$ $-40^{\circ}C \le T_A \le 85^{\circ}C$		35 40	45 50	nsec
Delay Time	t _{D2}	Figure 1	$T_A = 25^{\circ}C$ $-40^{\circ}C \le T_A \le 85^{\circ}C$	- -	35 40	45 50	nsec
Power Supply				•		•	•
Power Supply Current	IS	V _{IN} = 3 V V _{IN} = 0 V	V _{DD} = 16 V	_ _	0.5 0.1	1.0 0.15	mA

^{1.} Switching times are guaranteed by design.

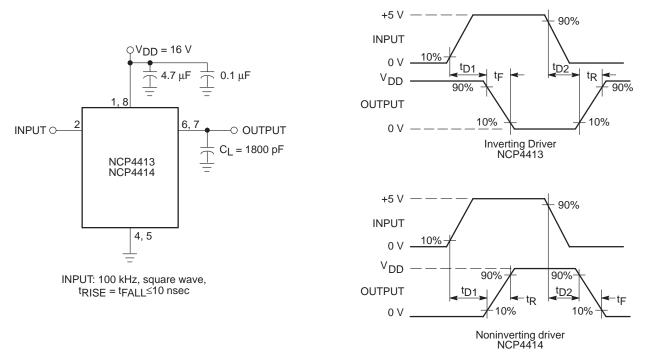


Figure 1. Switching Time Test Circuit

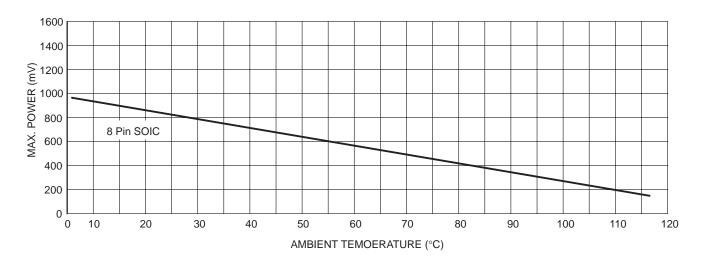


Figure 2. Thermal Derating Curves

TYPICAL CHARACTERISTICS

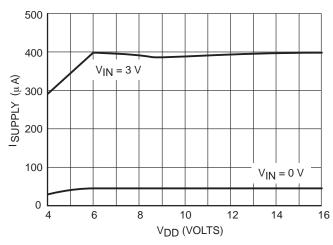


Figure 3. Quiescent Supply Current vs. Supply Voltage $T_A = 25^{\circ}C$

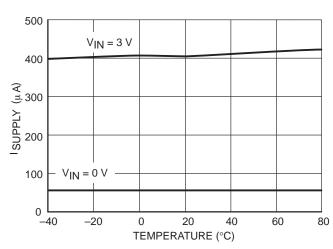


Figure 4. Quiescent Supply Current vs. Temperature
VSUPPLY = 16 V

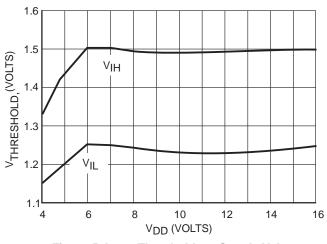


Figure 5. Input Threshold vs. Supply Voltage $TA = 25^{\circ}C$

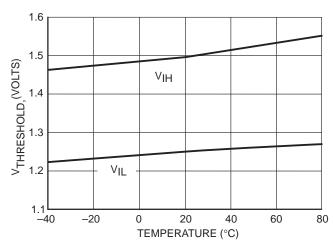


Figure 6. Input Threshold vs. Temperature VSUPPLY = 16 V

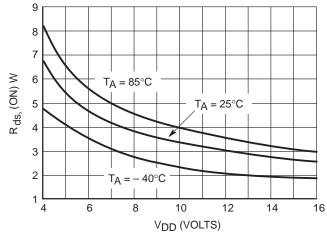


Figure 7. High-State Output Resistance

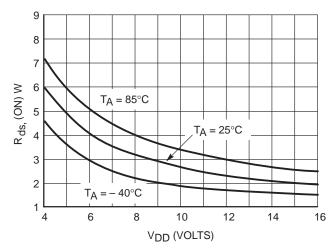


Figure 8. Low-State Output Resistance

TYPICAL CHARACTERISTICS

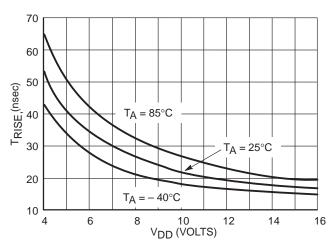


Figure 9. Rise Time vs. Supply Voltage CLOAD = 1800 pF

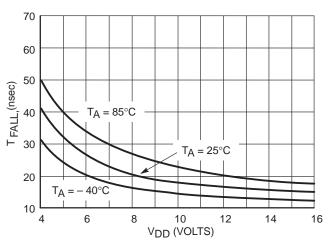


Figure 10. Fall Time vs. Supply Voltage CLOAD = 1800 pF

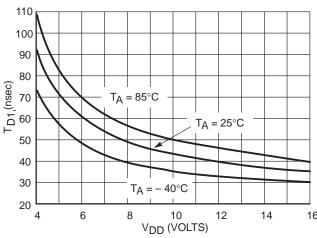


Figure 11. T_{D1} Propagation Delay vs. Supply Voltage CLOAD = 1800 pF

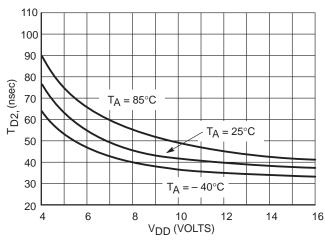


Figure 12. T_{D2} Propagation Delay vs. Supply Voltage C_{LOAD} = 1800 pF

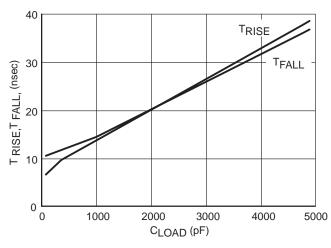


Figure 13. Rise and Fall Times vs. Capacitive Load T_A = 25°C, V_{DD} = 16 V

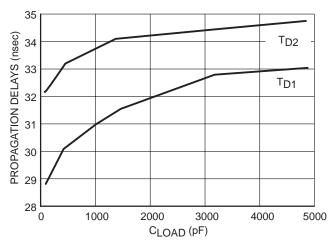
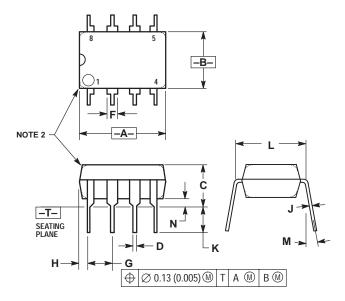


Figure 14. Propagation Delays vs. Capacitive Load TA = 25°C, V_{DD} = 16 V

PACKAGE DIMENSIONS

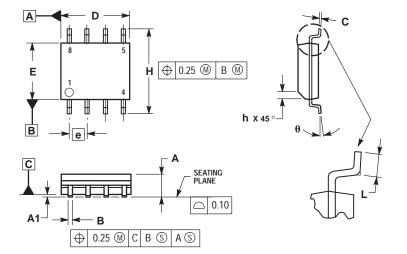
PDIP-8 **P SUFFIX** CASE 626-05 ISSUE K



- NOTES:
 1. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
 2. PACKAGE CONTOUR OPTIONAL (ROUND OR SQUARE CORNERS).
 3. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	9.40	10.16	0.370	0.400
В	6.10	6.60	0.240	0.260
С	3.94	4.45	0.155	0.175
D	0.38	0.51	0.015	0.020
F	1.02	1.78	0.040	0.070
G	2.54	BSC	0.100	BSC
Н	0.76	1.27	0.030	0.050
J	0.20	0.30	0.008	0.012
K	2.92	3.43	0.115	0.135
L	7.62	BSC	0.300	BSC
M		10°		10°
N	0.76	1.01	0.030	0.040

SO-8 **D SUFFIX** CASE 751-06 **ISSUE T**



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. DIMENSIONS ARE IN MILLIMETER.

 3. DIMENSION D AND E DO NOT INCLUDE MOLD PROTRUSION.

 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

 5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 TOTAL IN EXCESS OF THE B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		
DIM	MIN	MAX	
Α	1.35	1.75	
A1	0.10	0.25	
В	0.35	0.49	
С	0.19	0.25	
D	4.80	5.00	
Ε	3.80	4.00	
е	1.27 BSC		
Н	5.80	6.20	
h	0.25	0.50	
L	0.40	1.25	
A	N٥	70	

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